

## 2<sup>nd</sup> generation thinQ!<sup>™</sup> SiC Schottky Diode

## Features:

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## Applications:

- Revolutionary semiconductor material • SMPS, PFC, snubber
- Silicon CarbideSwitching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery
- High surge current capability

Chip Type	V <sub>BR</sub>	/ <sub>F</sub>	Die Size	Package
IDC04S60CE	600V	4A	1.146 x 0.968 mm <sup>2</sup>	sawn on foil

## **Mechanical Parameter**

	1				
Raster size	1.146x 0.968				
Anode pad size	0.909 x 0.731	mm <sup>2</sup>			
Area total	1.11				
Thickness	355	μm			
Wafer size	100	mm			
Max. possible chips per wafer	6190				
Passivation frontside	Photoimide				
Anode metal	3200 nm Al				
Cathode metal	Ni Ag –system suitable for epoxy and soft solder die bonding				
Die bond	Electrically conductive glue or solder				
Wire bond	Al, ≤ 350µm				
Reject ink dot size	Ø ≥ 0.3 mm				
Recommended storage environment	Store in original container, in dry nitrogen, in dark environment, < 6 month at an ambient temperature of 23°C				



### **Maximum Ratings**

Parameter	Symbol	Condition	Value	Unit	
Repetitive peak reverse voltage	V <sub>RRM</sub>	<i>T</i> <sub>vj</sub> = 25 °C	600	v	
DC blocking voltage	V <sub>DC</sub>		600		
Continuous forward current limited by $T_{vjmax}$	I <sub>F</sub>	<i>T</i> <sub>vj</sub> < 150°C	4		
Surge non repetitive forward current sine halfwave	I <sub>F,SM</sub>	<i>T</i> <sub>C</sub> =25°C, <i>t</i> <sub>P</sub> =10 ms	32	A	
Repetitive peak forward current limited by T <sub>vjmax</sub>	I <sub>F,RM</sub>	$T_{\rm C} = 100^{\circ}{\rm C}, \ T_{\rm vj} = 150^{\circ}{\rm C}, \ D=0.1$	18		
Non-repetitive peak forward current	I <sub>F,max</sub>	$T_{\rm C}$ =25°C, $t_{\rm p}$ =10µs	132		
Operating junction and storage temperature	T <sub>vj</sub> , T <sub>stg</sub>		-55+175	°C	

## Static Characteristics (tested on wafer)

Parameter	Symbol	Condi	Value			Unit	
	Symbol	Condi		min.	Тур.	max. 50 1.9	onne
Reverse current	I <sub>R</sub>	V <sub>R</sub> =600V	<i>T</i> <sub>vj</sub> = 25 °C		0.5	50	μA
Diode forward voltage	V <sub>F</sub>	I <sub>F</sub> =4A	<i>T</i> <sub>vj</sub> = 25 °C		1.7	1.9	V

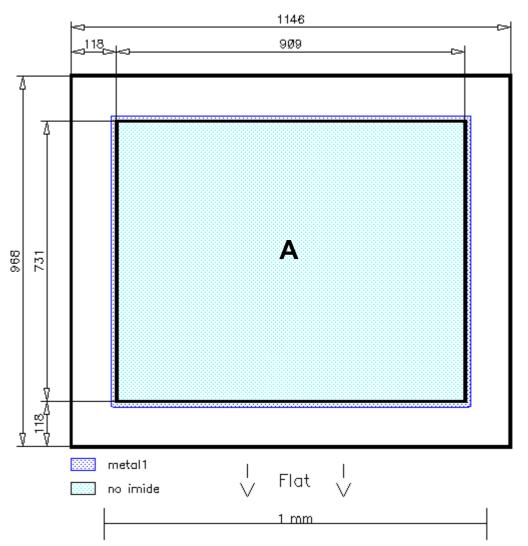
## **Dynamic Characteristics,** at $T_{vj}$ = 25 °C, unless otherwise specified, tested at component

Parameter	Symbol	Conditions		Value			Unit
Falamelei	Symbol			min.	Тур.	max.	Unit
Total capacitive charge	Q <sub>c</sub>	I <sub>F</sub> <=I <sub>F,max</sub> di/dt=200A/μs V <sub>R</sub> =400V	<i>T</i> <sub>vj</sub> = 150 °C		8		nC
Switching time <sup>1)</sup>	t <sub>c</sub>		<i>T</i> <sub>vj</sub> = 150 °C			<10	ns
Total capacitance	С	f=1MHz	V <sub>R</sub> =1V		130		
			V <sub>R</sub> =300V		20		pF
			V <sub>R</sub> =600V		20		

<sup>1)</sup>  $t_c$  is the time constant for the capacitive displacement current waveform (independent from  $T_{vj}$ ,  $I_{LOAD}$  and di/dt), different from  $t_{rr}$  which is dependent on  $T_{vj}$ ,  $I_{LOAD}$  and di/dt. No reverse recovery time constant  $t_{rr}$  due to absence of minority carrier injection



Chip drawing



Die-Size 1146 um x 968 um

A: Anode pad



### Description

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

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